

Title (en)

METHOD FOR MANUFACTURING A CRYSTALLINE LAYER OF PZT MATERIAL, AND SUBSTRATE FOR EPITAXIALLY GROWING A CRYSTALLINE LAYER OF PZT MATERIAL

Title (de)

VERFAHREN ZUR HERSTELLUNG EINER KRISTALLINEN SCHICHT AUS PZT-MATERIAL UND SUBSTRAT ZUM EPITAKTISCHEN WACHSEN EINER KRISTALLINEN SCHICHT AUS PZT-MATERIAL

Title (fr)

PROCEDE DE FABRICATION D'UNE COUCHE CRISTALLINE DE MATERIAU PZT ET SUBSTRAT POUR CROISSANCE PAR EPITAXIE D'UNE COUCHE CRISTALLINE DE MATERIAU PZT

Publication

EP 3775332 A1 20210217 (FR)

Application

EP 19722177 A 20190326

Priority

- FR 1800253 A 20180328
- IB 2019000201 W 20190326

Abstract (en)

[origin: WO2019186264A1] Method for manufacturing a crystalline layer of PZT material, including transferring a monocrystalline seed layer of SrTiO₃ material onto a support substrate of silicon material, followed by epitaxially growing the crystalline layer of PZT material.

IPC 8 full level

C30B 23/02 (2006.01); **C30B 25/18** (2006.01); **C30B 29/22** (2006.01); **C30B 33/06** (2006.01); **H01L 21/762** (2006.01)

CPC (source: EP KR US)

C30B 23/025 (2013.01 - EP KR); **C30B 25/183** (2013.01 - EP KR US); **C30B 29/22** (2013.01 - EP KR US); **C30B 33/06** (2013.01 - EP KR US); **H01L 21/76254** (2013.01 - EP KR); **H10N 30/079** (2023.02 - EP US); **H10N 30/708** (2024.05 - EP US); **H10N 30/8554** (2023.02 - US); **H10N 30/8548** (2023.02 - EP); **H10N 30/8554** (2023.02 - EP)

Designated contracting state (EPC)

AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)

BA ME

DOCDB simple family (publication)

WO 2019186264 A1 20191003; CN 111918986 A 20201110; EP 3775332 A1 20210217; FR 3079531 A1 20191004; FR 3079531 B1 20220318; JP 2021518321 A 20210802; JP 7451845 B2 20240319; KR 102636121 B1 20240213; KR 20200136436 A 20201207; SG 11202009530V A 20201029; US 11877514 B2 20240116; US 2021074906 A1 20210311; US 2023422619 A1 20231228

DOCDB simple family (application)

IB 2019000201 W 20190326; CN 201980021417 A 20190326; EP 19722177 A 20190326; FR 1800253 A 20180328; JP 2020549791 A 20190326; KR 20207030290 A 20190326; SG 11202009530V A 20190326; US 201917042657 A 20190326; US 202318464918 A 20230911